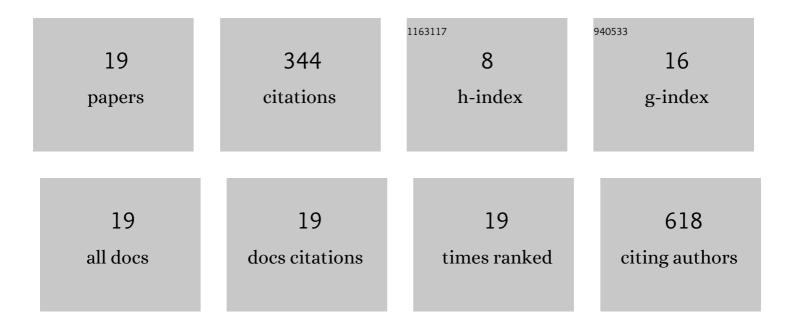
Patrick Ponath

List of Publications by Year in descending order

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| # | Article | IF | CITATIONS |
|----|--|------|-----------|
| 1 | Oxideâ€Based Optoelectronics. Physica Status Solidi (B): Basic Research, 2021, 258, 2000497. | 1.5 | 6 |
| 2 | Dielectric breakdown in epitaxial BaTiO3 thin films. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2020, 38, 044007. | 1.2 | 3 |
| 3 | Direct Observation of Large Atomic Polar Displacements in Epitaxial Barium Titanate Thin Films. Advanced Materials Interfaces, 2020, 7, 2000555. | 3.7 | 8 |
| 4 | Surface structure analysis of Eu Zintl template on Ge(001). Surface Science, 2018, 674, 94-102. | 1.9 | 9 |
| 5 | Polarization retention in ultra-thin barium titanate films on Ge(001). Applied Physics Letters, 2018, 112, . | 3.3 | 7 |
| 6 | Monolithic integration of patterned BaTiO3 thin films on Ge wafers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, . | 1.2 | 6 |
| 7 | Scavenging of oxygen from SrTiO3 during oxide thin film deposition and the formation of interfacial 2DEGs. Journal of Applied Physics, 2017, 121, . | 2.5 | 50 |
| 8 | Recent studies of oxide-semiconductor heterostructures using aberration-corrected scanning transmission electron microscopy. Journal of Materials Research, 2017, 32, 912-920. | 2.6 | 7 |
| 9 | Advances of the development of a ferroelectric field-effect transistor on Ge(001). , 2017, , . | | 1 |
| 10 | Integration of ferroelectric BaTiO3 with Ge: The role of a SrTiO3 buffer layer investigated using aberration-corrected STEM. Applied Physics Letters, 2017, 110, . | 3.3 | 5 |
| 11 | Aberration-corrected STEM Imaging and EELS Mapping of BaTiO3/SrTiO3 Interfacial Defects. Microscopy and Microanalysis, 2017, 23, 1598-1599. | 0.4 | 0 |
| 12 | Characterization of a ferroelectric BaTiO 3 /SrTiO 3 heterostructure with interface-induced polarization. Microscopy and Microanalysis, 2016, 22, 1508-1509. | 0.4 | 0 |
| 13 | Contradictory nature of Co doping in ferroelectricBaTiO3. Physical Review B, 2016, 94, . | 3.2 | 8 |
| 14 | Integrated films of transition metal oxides for information technology. Microelectronic Engineering, 2015, 147, 285-289. | 2.4 | 12 |
| 15 | Carrier density modulation in a germanium heterostructure by ferroelectric switching. Nature Communications, 2015, 6, 6067. | 12.8 | 75 |
| 16 | Analysis of the Pockels effect in ferroelectric barium titanate thin films on Si(0 0 1). Microelectronic Engineering, 2015, 147, 215-218. | 2.4 | 34 |
| 17 | Atomic and electronic structure of the ferroelectric BaTiO3/Ge(001) interface. Applied Physics Letters, 2014, 104, . | 3.3 | 45 |
| 18 | Critical differences in the surface electronic structure of Ge(001) and Si(001): <i>Ab initio</i> theory and angle-resolved photoemission spectroscopy. Physical Review B, 2014, 89, . | 3.2 | 31 |

| # | Article | IF | CITATIONS |
|----|--|-----|-----------|
| 19 | Preparation of a clean Ge(001) surface using oxygen plasma cleaning. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2013, 31, . | 1.2 | 37 |